

# LG-ITR9606

## DATA SHEET

SPEC.NO.: SZ19090505  
DATE: 2019/09/09  
REV. A/0

Approved By:

Checked By:

Prepared By:

## ■ Features

- . Fast response time
- . High analytic
- . Cut-off visible wavelength  $\lambda_p=940\text{nm}$
- . High sensitivity
- . Pb free
- . The product itself will remain within RoHS compliant version

## ■ Descriptions

The LG-ITR9606 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black Thermoplastic

Housing The phototransistor receives radiation from the IRED only .This is the normal Situation. But when an object is in between , phototransistor could not receives the radiation.

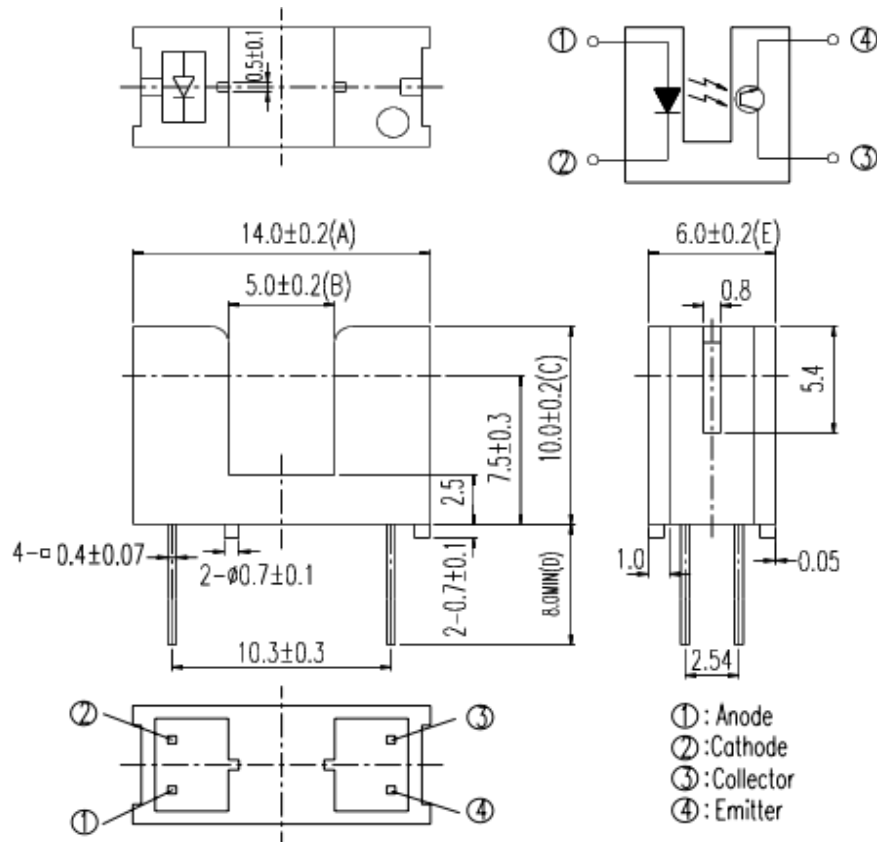
## ■ Applications

- . Mouse Copier
- . Switch Scanner
- . Floppy disk driver
- . Non-contact Switching
- . For Direct Board

## ■ Device Selection Guide

Device No.	Chip Material	LENS COLOR
IR	GaAlAs	Water Clear
PT	Silicon	Black

## Package Dimensions



### Notes:

1. All dimensions are in millimeters.
2. Tolerances unless dimensions  $\pm 0.25$ mm.
3. Lead spacing is measured where the lead emerge from the package .

## Absolute Maximum Ratings (Ta=25°C)

Parameter		Symbol	Ratings	Unit
Input	Power Dissipation at(or below) 25°C Free Air Temperature	Pd	100	mW
	Reverse Voltage	V <sub>R</sub>	5	V
	Forward Current	I <sub>F</sub>	50	mA
	Peak Forward Current (*1) Pulse width ≤ 100μs, Duty cycle=1%	I <sub>FP</sub>	1	A
	Collector Power Dissipation	P <sub>C</sub>	75	mW
Output	Collector Current	I <sub>C</sub>	50	mA
	Collector- Emitter Voltage	B V <sub>CEO</sub>	30	V
	Emitter- Collector Voltage	B V <sub>ECO</sub>	5	V
	Operating Temperature	Topr	-20~+65	°C
Storage Temperature	Tstg	-30~+70	°C	
Lead Soldering Temperature (*2)	T <sub>sold</sub>	260	°C	

(\* 1) tw=100 μsec., T=10 msec.

(\* 2) t=5 Sec

## Electro-Optical Characteristics (Ta=25°C)

Parameter		Symbol	Min.	Typ.	Max.	Unit	Conditions
Input	Forward Voltage	V <sub>F1</sub>	---	1.2	1.6	V	I <sub>F</sub> =20mA
		V <sub>F2</sub>	---	1.4	1.85		I <sub>F</sub> =100mA, tp=100μs, tp/T=0.01
		V <sub>F3</sub>	---	2.6	4.0		I <sub>F</sub> =1A, tp=100μs, tp/T=0.01
	Reverse Current	I <sub>R</sub>	---	---	10	μA	V <sub>R</sub> =5V
	Peak Wavelength	λ <sub>p</sub>	---	940	---	nm	I <sub>F</sub> =20mA
	View Angle	291/2	---	60	---	Deg	I <sub>F</sub> =20mA
Output	Dark Current	I <sub>CEO</sub>	---	---	100	nA	V <sub>CE</sub> =20V, Ee=0mW/cm <sup>2</sup>
	C-E Saturation Voltage	V <sub>CE(sat)</sub>	---	---	0.4	V	I <sub>C</sub> =2mA, Ee=1mW/cm <sup>2</sup>
Transfer Characteristics	Collect Current	I <sub>C(ON)</sub>	0.5	---	---	mA	V <sub>CE</sub> =5V, I <sub>F</sub> =20mA
	Rise time	t <sub>r</sub>	---	15	---	μsec	V <sub>CE</sub> =5V
	Fall time	t <sub>f</sub>	---	15	---	μsec	I <sub>C</sub> =1mA

## Typical Electrical/Optical/Characteristics Curves for IR

Fig.1 Forward Current vs. Ambient Temperature

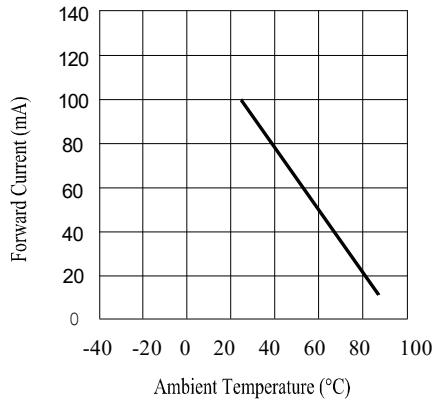


Fig.2 Spectral Distribution

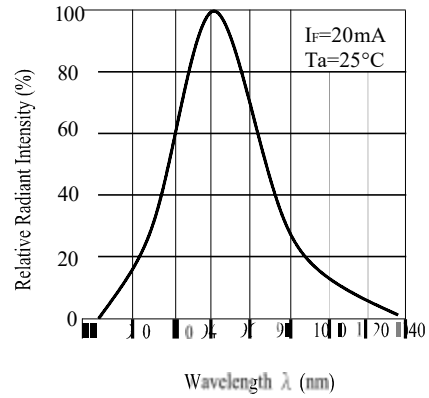


Fig.3 Relative Intensity vs. Forward Current

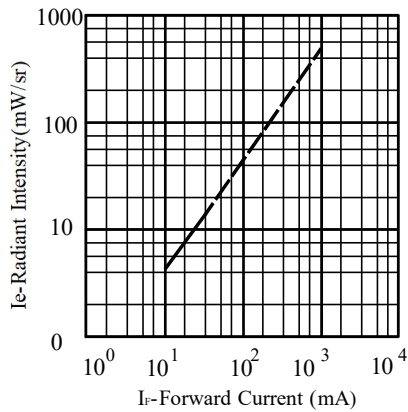


Fig.4 Relative Radiant Intensity vs. Angular Displacement

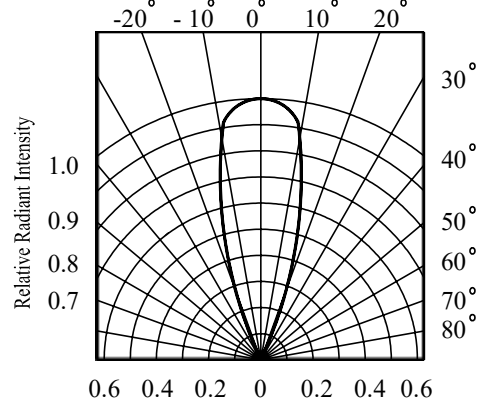


Fig.5 Relative Intensity vs. Ambient Temperature(°C)

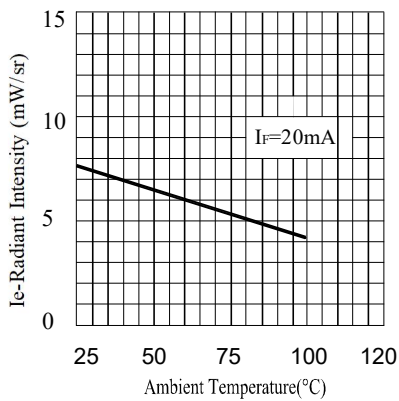
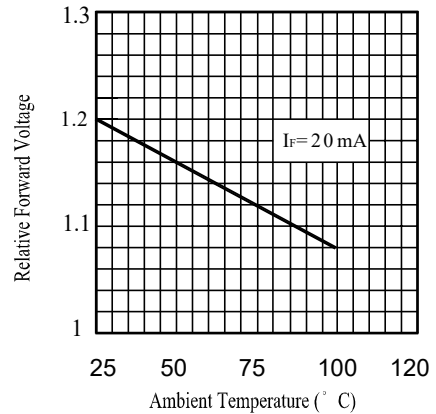


Fig.6 Forward Current vs. Ambient Temperature(°C)



Typical Electrical/Optical/Characteristics Curves for PT

Fig. 1 Collector Power Dissipation vs. Ambient Temperature

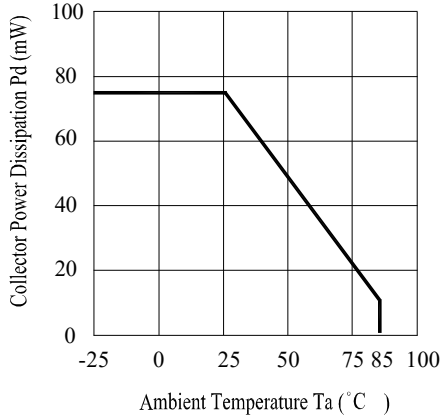


Fig. 2 Spectral Sensitivity

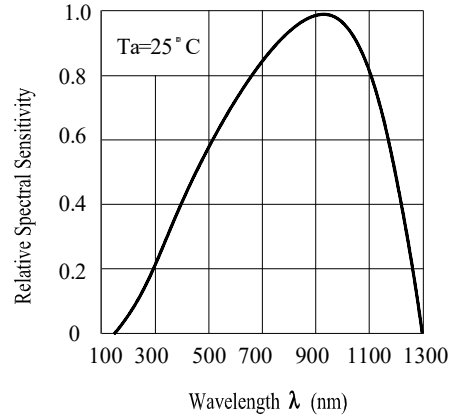


Fig. 3 Relative Collector Current vs. Ambient Temperature

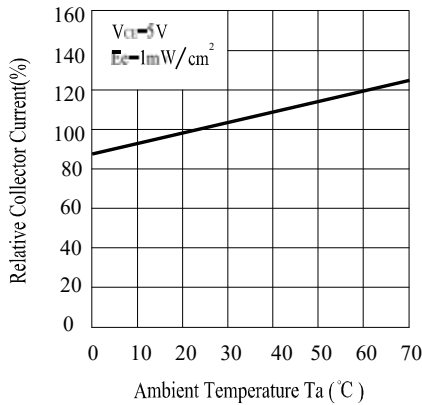


Fig. 4 Collector Current vs. Irradiance

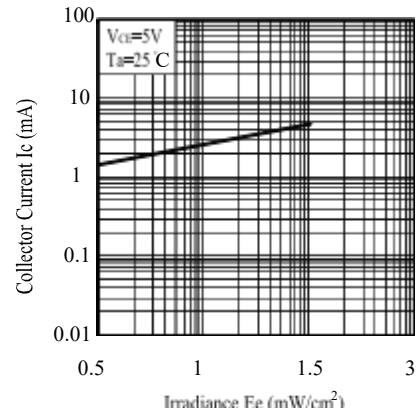


Fig. 5 Collector Dark Current vs. Ambient Temperature

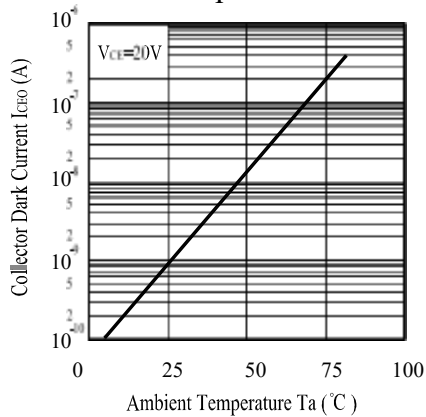


Fig. 6 Collector Current vs. Collector-Emitter Voltage

